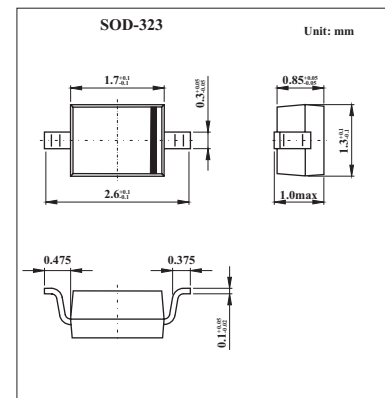


Silicon Epitaxial Planar Diode

1SV245

■ Features

- High Capacitance Ratio: $C_{2V}/C_{25V} = 5.7$ (Typ.)
- Low Series Resistance: $r_s = 1.2 \Omega$ (Typ.)
- Excellent C-V Characteristics, and Small Tracking Error.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Peak Reverse Voltage	V_{RM}	35($R_L = 10 \text{ K } \Omega$)	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R = 1 \mu\text{A}$	30			V
Reverse Current	I_R	$V_R = 28 \text{ V}$			10	nA
Capacitance	C_{2V}	$f = 1 \text{ MHz}; V_R = 2 \text{ V}$	3.31		4.55	pF
	C_{25V}	$f = 1 \text{ MHz}; V_R = 25 \text{ V}$	0.61		0.77	
Capacitance Ratio	C_{2V}/C_{25V}		5	5.7	6.5	
Series Resistance	r_s	$V_R = 1 \text{ V}, f = 470 \text{ MHz}$		1.2	2.0	Ω

Note :

Unites are compounded in one package and are mated to 6.0%

$$\frac{C(\text{Max.})-C(\text{Min.})}{C(\text{Min.})} \leq 0.06$$

($V_R = 2 \sim 25 \text{ V}$)

■ Marking

Marking	T3
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